



CS684 TO3

PNP SILICON DARLINGTON POWER TRANSISTORS

PNP epitaxial-base transistors in monolithic Darlington circuit for audio and video applications.

They are mounted in Jedec TO-3 metal package.

Compliance to RoHS.

CS684 is the BD684 in TO3 package.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit
$-V_{CEO}$	Collector-Emitter Voltage	140	V
$-V_{CBO}$	Collector-Base Voltage	140	V
$-V_{EBO}$	Emitter-Base Voltage	5	V
$-I_C$	Collector Current	4	A
		6	
$-I_B$	Base current (peak value)	0.1	A
P_T	Total power Dissipation <small>@ $T_{mb} = 25^\circ\text{C}$</small>	65	Watts
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{Stg}	Storage Temperature	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-mb}	Thermal Resistance, Junction to mounting base	3.12	K/W
R_{thJ-a}	Thermal Resistance, Junction to ambient in free air	100	K/W



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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

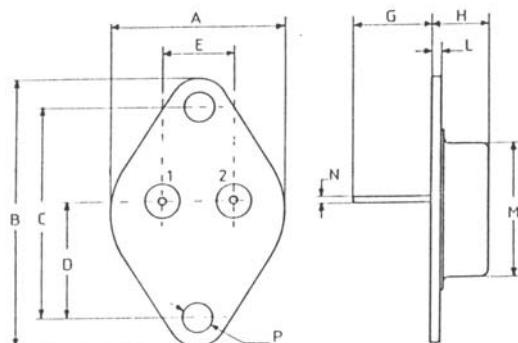
Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit
-I _{CBO}	Collector cut-off current	I _E =0 , -V _{CB} = -V _{CEOMAX} =140 V I _E =0 , -V _{CB} = -1/2V _{CBOMAX} = 70V, T _j = 150°C	-	-	0,2	mA
-I _{CEO}	Collector cut-off current	I _B =0 , -V _{CE} = -1/2V _{CEOMAX} =70 V	-	-	1	mA
-I _{EBO}	Emitter cut-off current	I _C =0, -V _{EB} =5 V	-	-	0,2	mA
-V _{CE(SAT)}	Collector-Emitter saturation Voltage	I _C =1,5 A , I _B =6 mA	-	-	5	mA
h _{FE}	DC Current Gain	-V _{CE} =3 V , -I _C =500 mA	-	2000	-	
		-V _{CE} =3 V , -I _C =1,5 A	750	-	-	
		-V _{CE} =3 V , -I _C =4 A	-	750	-	
-V _{BE}	Base-Emitter Voltage(1&2)	-V _{CE} =3 V , -I _C =1,5 A	-	-	2,5	V
h _{fe}	Small signal current gain	-V _{CE} =3 V , -I _C =1,5 A, f= 1 MHz	10	-	-	
f _{hfe}	Ut-off frequency	-V _{CE} =3 V , -I _C =1,5 A	-	60	-	kHz
V _F	Diode forward voltage	I _F =1,5 A	-	1,5	-	V
-I _(SB)	Second-breakdown collector current	-V _{CE} =50 V, t _p = 20ms,non rep., without heatsink	0,8	-	-	A
t _{on}	Turn-on time	I _{con} = 1,5A, I _{bon} = -I _{boff} = 6mA, V _{CC} =30V	-	0,8	2	
t _{off}	Turn-off time		-	4,5	8	μs

1. Measured under pulse conditions :t_p <300μs, δ <2%.

2. V_{BE} decreases by about 3,6 mV/K with increasing temperature.

MECHANICAL DATA CASE TO-3

DIMENSIONS		
	mm	inches
A	25,51	1,004
B	38,93	1,53
C	30,12	1,18
D	17,25	0,68
E	10,89	0,43
G	11,62	0,46
H	8,54	0,34
L	1,55	0,6
M	19,47	0,77
N	1	0,04
P	4,06	0,16



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector